

L Number	Hits	Search Text	DB	Time stamp
1	102564	DRAM or (dynamic adj5 random adj5 access adj5 memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 02:35
2	9980	(DRAM or (dynamic adj5 random adj5 access adj5 memory)) same (memory adj3 cell\$1) same transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 02:59
3	7163	((DRAM or (dynamic adj5 random adj5 access adj5 memory)) same (memory adj3 cell\$1) same transistor) same capacitor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:06
5	85	((((DRAM or (dynamic adj5 random adj5 access adj5 memory)) same (memory adj3 cell\$1) same transistor) same capacitor\$1) same test\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:41
7	59	(((((DRAM or (dynamic adj5 random adj5 access adj5 memory)) same (memory adj3 cell\$1) same transistor) same capacitor\$1) same test\$3) and 365/\$7.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:11
8	38	(((((DRAM or (dynamic adj5 random adj5 access adj5 memory)) same (memory adj3 cell\$1) same transistor) same capacitor\$1) same test\$3) and 365/201.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:11
10	10	(((((DRAM or (dynamic adj5 random adj5 access adj5 memory)) same (memory adj3 cell\$1) same transistor) same capacitor\$1) same test\$3) and 365/201.ccls.) and resistanc\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:16
11	16	(DRAM or (dynamic adj5 random adj5 access adj5 memory)) and (resistance near6 (selection adj3 transistor)) and (storage adj3 capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:36
12	1	((DRAM or (dynamic adj5 random adj5 access adj5 memory)) and (resistance near6 (selection adj3 transistor)) and (storage adj3 capacitor)) and (buried adj3 strap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:19
13	5	((DRAM or (dynamic adj5 random adj5 access adj5 memory)) and (resistance near6 (selection adj3 transistor)) and (storage adj3 capacitor)) and buried	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:35
14	49	(DRAM or (dynamic adj5 random adj5 access adj5 memory)) and resistance and (selection adj3 transistor) and (storage adj3 capacitor) and buried	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:37
15	10	((DRAM or (dynamic adj5 random adj5 access adj5 memory)) and resistance and (selection adj3 transistor) and (storage adj3 capacitor) and buried) and 365/\$7.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:40
16	1	((DRAM or (dynamic adj5 random adj5 access adj5 memory)) and resistance and (selection adj3 transistor) and (storage adj3 capacitor) and buried) and 365/199.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:39

18	6	((DRAM or (dynamic adj5 random adj5 access adj5 memory)) and resistance and (selection adj3 transistor) and (storage adj3 capacitor) and buried) and 365/149.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:40
19	9	"6426526"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:41
20	15	rosskopf-valentin.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:41
21	2	rosskopf-valentin-\$.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:41
22	8	felber-andreas.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:41
23	0	felber-andreas-\$.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:41
24	2	sukman-sibina.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:42
25	0	sukman-sibina-\$.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/01 03:42